

**IN THE CLAIMS:**

1 - 19. (canceled)

20. (previously presented) A manufacturing method of a silicon wafer, in which a silicon wafer that has been sliced from a silicon single crystal is heat-treated in an oxidizing atmosphere, wherein

assuming that a temperature at which said heat treatment is carried out in said oxidizing atmosphere is denoted as  $T(^{\circ}\text{C})$  and an interstitial oxygen concentration is denoted as  $[\text{O}_i]$  (atoms/cm<sup>3</sup>), said manufacturing method of the silicon wafer characterized in that a relation between said temperature  $T$  and said interstitial oxygen concentration  $[\text{O}_i]$  satisfies the following formula:

$$[\text{O}_i] \leq 2.123 \times 10^{21} \exp(-1.035/k(T+273)),$$

where, said interstitial oxygen concentration is a value measured in accordance with FT-IR method (ASTM F-121, 1979) and the  $k$  is the Boltzmann's constant,  $8.617 \times 10^{-5}$  (eV/K).

21. (previously presented) A manufacturing method of a silicon wafer in accordance with claim 20, in which a single crystal doped with phosphorus by a neutron irradiation is used as said silicon single crystal.

22. (previously presented) A manufacturing method of a silicon wafer in accordance with claim 20, in which a single crystal doped with nitrogen by a concentration of  $2 \times 10^{13}$  atoms/cm<sup>3</sup> or more and/or a single crystal doped with carbon by a concentration of  $5 \times 10^{16}$  atoms/cm<sup>3</sup> or more is used as said silicon single crystal.

23. (canceled)

24. previously presented) A manufacturing method of a silicon wafer in accordance with claim 20, in which the silicon wafer is mirror-polished after said heat treatment in said oxidizing atmosphere.

25. (previously presented) A manufacturing method of a silicon wafer in accordance with claim 21, in which the silicon wafer is mirror-polished after said heat treatment in said oxidizing atmosphere.

26. (previously presented) A manufacturing method of a silicon wafer in accordance with claim 22, in which the silicon

wafer is mirror-polished after said heat treatment in said oxidizing atmosphere.

27. (canceled)

28. (previously presented) A manufacturing method of a SOI wafer, in which a SOI wafer is manufactured by using said silicon wafer manufactured by said method as defined in claim 24 for an active layer side wafer.

29. (previously presented) A manufacturing method of a SOI wafer, in which a SOI wafer is manufactured by using said silicon wafer manufactured by said method as defined in claim 25 for an active layer side wafer.

30. (previously presented) A manufacturing method of a SOI wafer, in which a SOI wafer is manufactured by using said silicon wafer manufactured by said method as defined in claim 26 for an active layer side wafer.

31. (canceled)

32. (previously presented) A manufacturing method of a SOI wafer, in which a buried oxide film is formed by applying a heat treatment to an active layer side silicon wafer in an oxidizing atmosphere, and said active layer side silicon wafer is then bonded to a supporting side wafer with said buried oxide layer interposed therebetween thus to manufacture a bonded SOI wafer, wherein

assuming that a temperature at which said heat treatment is applied to said active layer side silicon wafer in said oxidizing atmosphere is denoted as  $T(^{\circ}\text{C})$  and an interstitial oxygen concentration of said active layer side silicon wafer is denoted as  $[\text{O}_i]$  (atoms/cm<sup>3</sup>), said manufacturing method of the SOI wafer characterized in that a relation between said heat treatment temperature  $T$  and said interstitial oxygen concentration  $[\text{O}_i]$  of said active layer side silicon wafer satisfies the following formula:

$$[\text{O}_i] \leq 2.123 \times 10^{21} \exp(-1.035/k(T+273)),$$

where, said interstitial oxygen concentration is a value measured in accordance with FT-IR method (ASTM F-121, 1979) and the  $k$  is the Boltzmann's constant,  $8.617 \times 10^{-5}$  (eV/K).

33. (previously presented) A manufacturing method of a SOI wafer in accordance with claim 32, in which said active layer side

silicon wafer is fabricated by using a silicon single crystal doped with phosphorus by neutron irradiation.

34. (previously presented) A manufacturing method of a SOI wafer in accordance with claim 32, in which said active layer side silicon wafer is fabricated by using a silicon single crystal doped with nitrogen by a concentration of  $2 \times 10^{13}$  atoms/cm<sup>3</sup> of more and/or by using a silicon single crystal doped with carbon by a concentration of  $5 \times 10^{16}$  atoms/cm<sup>3</sup> or more.

35. (canceled)

36. (previously presented) A manufacturing method of a SOI wafer, in which an active layer side silicon wafer is bonded to a supporting side wafer with an insulating film interposed therebetween and then a heat treatment for enhancing a bonding strength is applied to thus bonded wafer in an oxidizing atmosphere to thereby manufacture a bonded SOI wafer, wherein

assuming that a temperature at which said heat treatment for enhancing the bonding strength is carried out in said oxidizing atmosphere is denoted as  $T(^{\circ}\text{C})$  and an interstitial oxygen concentration of said active layer side silicon wafer is denoted as

[Oi] (atoms/cm<sup>3</sup>), said manufacturing method of the SOI wafer characterized in that a relation between said temperature T and said interstitial oxygen concentration [Oi] satisfies the following formula:

$$[Oi] \leq 2.123 \times 10^{21} \exp(-1.035/k(T+273)),$$

where, said interstitial oxygen concentration is a value measured in accordance with FT-IR method (ASTM F-121, 1979) and the k is the Boltzmann's constant,  $8.617 \times 10^{-5}$  (eV/K).

37. (previously presented) A manufacturing method of a SOI wafer in accordance with claim 36, in which said active layer side silicon wafer is fabricated by using a silicon single crystal doped with phosphorus by neutron irradiation.

38. (previously presented) A manufacturing method of a SOI wafer in accordance with claim 36, in which said active layer side silicon wafer is fabricated by using a silicon single crystal doped with nitrogen by a concentration of  $2 \times 10^{13}$  atoms/cm<sup>3</sup> or more and/or by using a silicon single crystal doped with carbon by a concentration of  $5 \times 10^{16}$  atoms/cm<sup>3</sup> or more.

39. (canceled)

40. (previously presented) A manufacturing method of a SOI wafer, comprising the steps of:

fabricating an active layer side silicon wafer by firstly applying an oxidizing heat treatment to a silicon wafer, which satisfies the following formula representing a relation between a heat treatment temperature  $T$  and an interstitial oxygen concentration  $[O_i]$ :

$$[O_i] \leq 2.123 \times 10^{21} \exp(-1.035/k(T+273)),$$

where,  $T(^{\circ}\text{C})$  is the temperature at which said heat treatment is carried out in an oxidizing atmosphere, and  $[O_i]$  (atoms/cm<sup>3</sup>) is the interstitial oxygen concentration in the silicon wafer, wherein said interstitial oxygen concentration is a value measured in accordance with FT-IR method (ASTM F-121, 1979) and the  $k$  is the Boltzmann's constant,  $8.617 \times 10^{-5}$  (eV/K), and by secondly removing an oxide film and applying a mirror-polishing;

forming an ion implanted layer in said active layer side silicon wafer by forming an oxide film on said active layer side silicon wafer, and ion-implanting via said oxide film;

subsequently, forming a bonded wafer by bonding said active layer side silicon wafer to a supporting side wafer with said oxide film interposed therebetween; and

then, separating a part of said active layer side silicon wafer from a boundary defined by said ion implanted layer by holding said bonded wafer at a predetermined temperature to thereby apply a heat treatment thereto.

41. (previously presented) A manufacturing method of a SOI wafer in accordance with claim 40, in which a surface of the separated active layer side wafer is mirror-polished so that it can be used repeatedly as a substrate for forming a new active layer of the SOI wafer.

42. (previously presented) A manufacturing method of a SOI wafer in accordance with claim 40, in which said active layer side silicon wafer is fabricated by using a silicon single crystal doped with phosphorus by neutron irradiation.

43. (previously presented) A manufacturing method of a SOI wafer in accordance with claim 41, in which said active layer side silicon wafer is fabricated by using a silicon single crystal doped with phosphorus by neutron irradiation.



44. (previously presented) A manufacturing method of a SOI wafer in accordance with claim 40, in which said active layer side silicon wafer is fabricated by using a silicon single crystal doped with nitrogen by a concentration of  $2 \times 10^{13}$  atoms/cm<sup>3</sup> or more and/or by using a silicon single crystal doped with carbon by a concentration of  $5 \times 10^{16}$  atoms/cm<sup>3</sup> or more.

45. (previously presented) A manufacturing method of a SOI wafer in accordance with claim 41, in which said active layer side silicon wafer is fabricated by using a silicon single crystal doped with nitrogen by a concentration of  $2 \times 10^{13}$  atoms/cm<sup>3</sup> or more and/or by using a silicon single crystal doped with carbon by a concentration of  $5 \times 10^{16}$  atoms/cm<sup>3</sup> or more.

46 - 47. (canceled)